



Integrated Device Technology, Inc.

# CMOS STATIC RAM 1 MEG (256K x 4-BIT)

IDT71028S70

### FEATURES:

- 256K x 4 CMOS static RAM
- Equal access and cycle times
  - Commercial: 70ns
- One Chip Select plus one Output Enable pin
- Bidirectional data Inputs and outputs directly TTL-compatible
- Low power consumption via chip deselect
- Available in 400 mil Plastic SOJ package

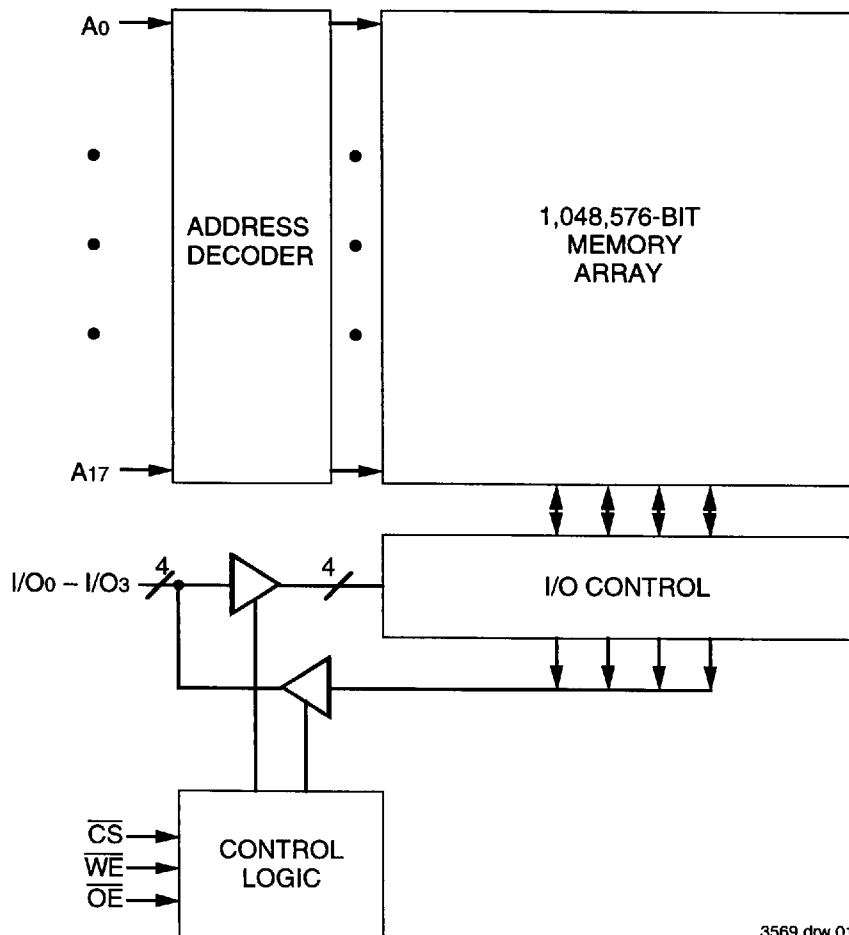
### DESCRIPTION:

The IDT71028 is a 1,024,576-bit medium-speed static RAM organized as 256K x 4. It is fabricated using IDT's high-performance, high-reliability CMOS technology. This state-of-the-art technology, combined with innovative circuit design techniques, provides a cost-effective solution for your memory needs.

The IDT71028 has an output enable pin which operates as fast as 30ns, with address access times as fast as 70ns. All bidirectional inputs and outputs of the IDT71028 are TTL-compatible and operation is from a single 5V supply. Fully static asynchronous circuitry is used, requiring no clocks or refresh for operation.

The IDT71028 is packaged in 28-pin 400 mil Plastic SOJ package.

### FUNCTIONAL BLOCK DIAGRAM



3569 drw 01

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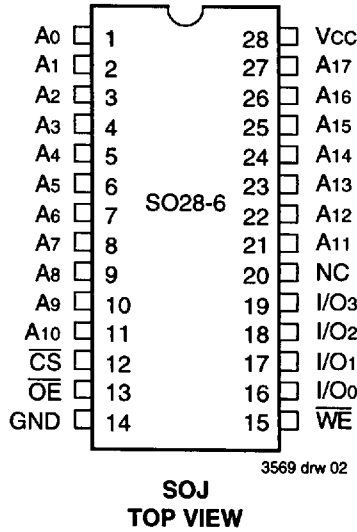
COMMERCIAL TEMPERATURE RANGE

MAY 1996

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3569/-

**PIN CONFIGURATION**



**ABSOLUTE MAXIMUM RATINGS<sup>(1)</sup>**

Symbol	Rating	Com'l.	Unit
VTERM <sup>(2)</sup>	Terminal Voltage with Respect to GND	-0.5 to +7.0	V
TA	Operating Temperature	0 to +70	°C
TBIAS	Temperature Under Bias	-55 to +125	°C
TSTG	Storage Temperature	-55 to +125	°C
PT	Power Dissipation	1.25	W
IOUT	DC Output Current	50	mA

**NOTES:**

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- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- VTERM must not exceed Vcc + 0.5V.

**TRUTH TABLE<sup>(1,2)</sup>**

CS	OE	WE	I/O	Function
L	L	H	DATAOUT	Read Data
L	X	L	DATAIN	Write Data
L	H	H	High-Z	Output Disabled
H	X	X	High-Z	Deselected - Standby (ISB)
VHC <sup>(3)</sup>	X	X	High-Z	Deselected - Standby (ISB1)

**NOTES:**

3569 tbl 01

- H = VIH, L = VIL, x = Don't care.
- VLC = 0.2V, VHC = Vcc - 0.2V.
- Other inputs ≥VHC or ≤VLC.

**CAPACITANCE**

(TA = +25°C, f = 1.0MHz, SOJ package)

Symbol	Parameter <sup>(1)</sup>	Conditions	Max.	Unit
CIN	Input Capacitance	VIN = 3dV	8	pF
CIO	I/O Capacitance	VOUT = 3dV	8	pF

**NOTE:**

3569 tbl 03

- This parameter is guaranteed by device characterization, but not production tested.

**RECOMMENDED DC OPERATING CONDITIONS**

Symbol	Parameter	Min.	Typ.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Supply Voltage	0	0	0	V
VIH	Input High Voltage	2.2	—	Vcc+0.5	V
VIL	Input Low Voltage	-0.5 <sup>(1)</sup>	—	0.8	V

**NOTE:**

3569 tbl 04

- VIL (min.) = -1.5V for pulse width less than 10ns, once per cycle.

**DC ELECTRICAL CHARACTERISTICS**

Vcc = 5.0V ± 10%

Symbol	Parameter	Test Condition	IDT71028		Unit
			Min.	Max.	
II <sub>L</sub>	Input Leakage Current	Vcc = Max., VIN = GND to Vcc	—	5	μA
II <sub>O</sub>	Output Leakage Current	Vcc = Max., CS = VIH, VOUT = GND to Vcc	—	5	μA
VOL	Output Low Voltage	IO <sub>L</sub> = 8mA, Vcc = Min.	—	0.4	V
VOH	Output High Voltage	IO <sub>H</sub> = -4mA, Vcc = Min.	2.4	—	V

3569 tbl 05

### DC ELECTRICAL CHARACTERISTICS<sup>(1)</sup>

( $V_{CC} = 5.0V \pm 10\%$ ,  $V_{LC} = 0.2V$ ,  $V_{HC} = V_{CC} - 0.2V$ )

Symbol	Parameter	71028S70		
		Com'l.	Mil.	Unit
I <sub>CC</sub>	Dynamic Operating Current, CS2 ≥ V <sub>IH</sub> and CS2 ≥ V <sub>IH</sub> and CS1 ≤ V <sub>IL</sub> , Outputs Open, V <sub>CC</sub> = Max., f = f <sub>MAX</sub> <sup>(2)</sup>	140	—	mA
I <sub>SB</sub>	Standby Power Supply Current (TTL Level) CS1 ≥ V <sub>IH</sub> or CS2 ≤ V <sub>IL</sub> , Outputs Open, V <sub>CC</sub> = Max., f = f <sub>MAX</sub> <sup>(2)</sup>	35	—	mA
I <sub>SB1</sub>	Full Standby Power Supply Current (CMOS Level) CS1 ≥ V <sub>HC</sub> , or CS2 ≤ V <sub>LC</sub> Outputs Open, V <sub>CC</sub> = Max., f = 0 <sup>(2)</sup> , V <sub>IN</sub> ≤ V <sub>LC</sub> or V <sub>IN</sub> ≥ V <sub>HC</sub>	10	—	mA

**NOTES:**

- All values are maximum guaranteed values.
- f<sub>MAX</sub> = 1/trc (all address inputs are cycling at f<sub>MAX</sub>): f = 0 means no address input lines are changing.

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### AC TEST CONDITIONS

Input Pulse Levels	GND to 3.0V
Input Rise/Fall Times	3ns
Input Timing Reference Levels	1.5V
Output Reference Levels	1.5V
AC Test Load	See Figures 1 and 2

3569 tbl 07

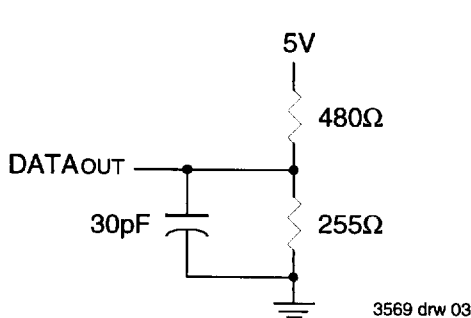
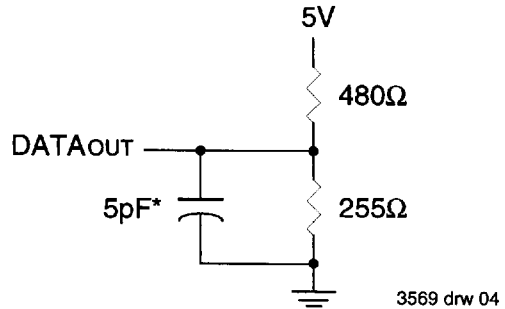


Figure 1. AC Test Load



\*Including jig and scope capacitance.  
 Figure 2. AC Test Load  
 (for t<sub>CLZ</sub>, t<sub>OLZ</sub>, t<sub>CHZ</sub>, t<sub>OHZ</sub>, t<sub>OW</sub>, and t<sub>WHZ</sub>)

**AC ELECTRICAL CHARACTERISTICS** ( $V_{CC} = 5.0V \pm 10\%$ , Commercial Temperature Range)

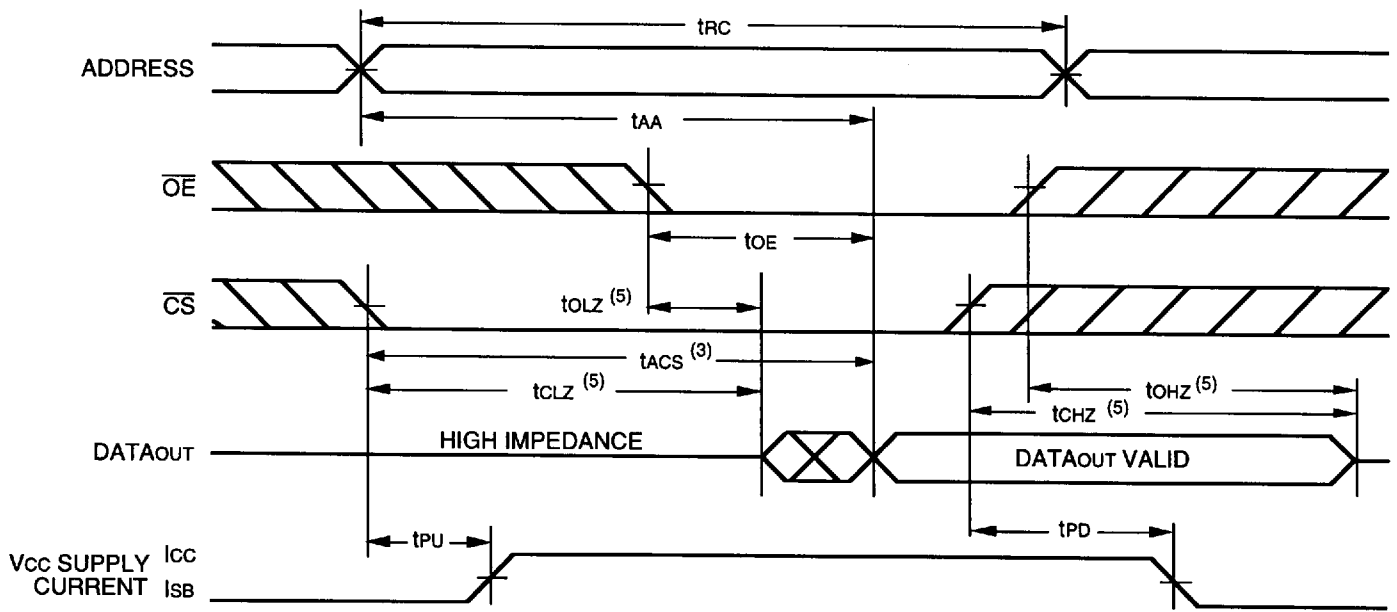
Symbol	Parameter	71028S70		Unit
		Min.	Max.	
<b>Read Cycle</b>				
t <sub>RC</sub>	Read Cycle Time	70	—	ns
t <sub>AA</sub>	Address Access Time	—	70	ns
t <sub>ACS</sub>	Chip Select Access Time	—	70	ns
t <sub>CLZ</sub> <sup>(2)</sup>	Chip Select to Output in Low-Z	3	—	ns
t <sub>CHZ</sub> <sup>(2)</sup>	Chip Deselect to Output in High-Z	0	30	ns
t <sub>OE</sub>	Output Enable to Output Valid	—	30	ns
t <sub>OLZ</sub> <sup>(2)</sup>	Output Enable to Output in Low-Z	0	—	ns
t <sub>OHZ</sub> <sup>(2)</sup>	Output Disable to Output in High-Z	0	30	ns
t <sub>OH</sub>	Output Hold from Address Change	4	—	ns
t <sub>PU</sub> <sup>(2)</sup>	Chip Select to Power-Up Time	0	—	ns
t <sub>PD</sub> <sup>(2)</sup>	Chip Deselect to Power-Down Time	—	70	ns
<b>Write Cycle</b>				
t <sub>WC</sub>	Write Cycle Time	70	—	ns
t <sub>AW</sub>	Address Valid to End-of-Write	60	—	ns
t <sub>CW</sub>	Chip Select to End-of-Write	60	—	ns
t <sub>AS</sub>	Address Set-up Time	0	—	ns
t <sub>WP</sub>	Write Pulse Width	45	—	ns
t <sub>WR</sub>	Write Recovery Time	0	—	ns
t <sub>DW</sub>	Data Valid to End-of-Write	30	—	ns
t <sub>DH</sub>	Data Hold Time	0	—	ns
t <sub>OW</sub> <sup>(2)</sup>	Output Active from End-of-Write	5	—	ns
t <sub>WHZ</sub> <sup>(2)</sup>	Write Enable to Output in High-Z	0	30	ns

**NOTES:**

1. 0°C to +70°C temperature range only.
2. This parameter guaranteed with the AC load (Figure 2) by device characterization, but is not production tested.

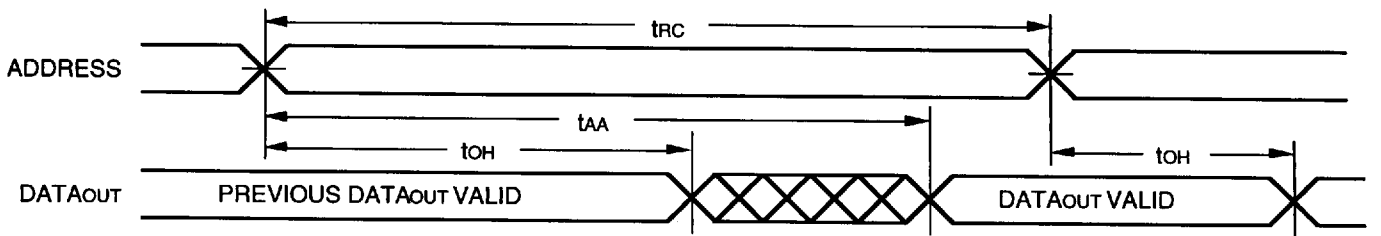
3569 tbl 08

**TIMING WAVEFORM OF READ CYCLE NO. 1<sup>(1)</sup>**



3569 drw 05

**TIMING WAVEFORM OF READ CYCLE NO. 2<sup>(1,2,4)</sup>**

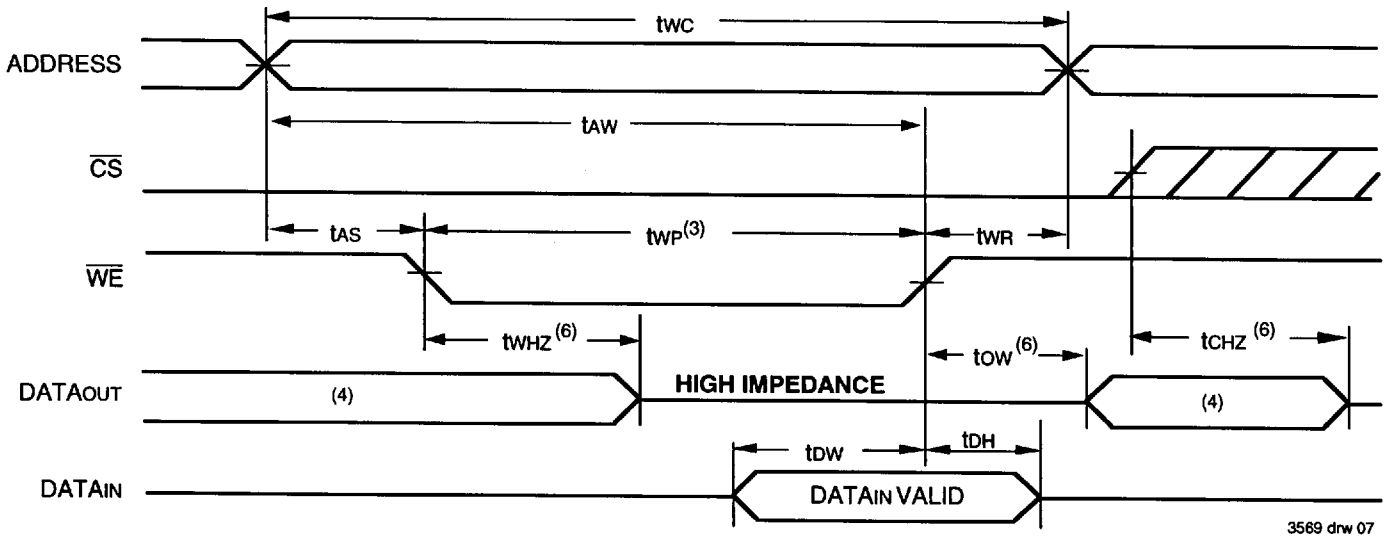


3569 drw 6

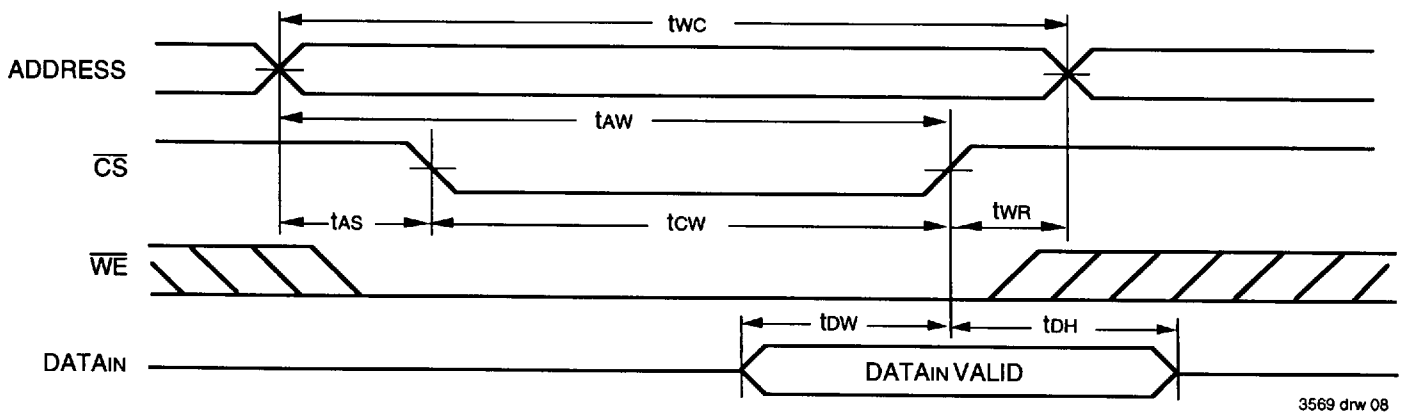
**NOTES:**

1.  $\overline{WE}$  is HIGH for Read Cycle.
2. Device is continuously selected,  $\overline{CS}$  is LOW.
3. Address must be valid prior to or coincident with the later of  $\overline{CS}$  transition LOW; otherwise  $t_{AA}$  is the limiting parameter.
4.  $\overline{OE}$  is LOW.
5. Transition is measured  $\pm 200\text{mV}$  from steady state.

**TIMING WAVEFORM OF WRITE CYCLE NO.1 ( $\overline{WE}$  CONTROLLED TIMING)<sup>(1,2,3,5)</sup>**



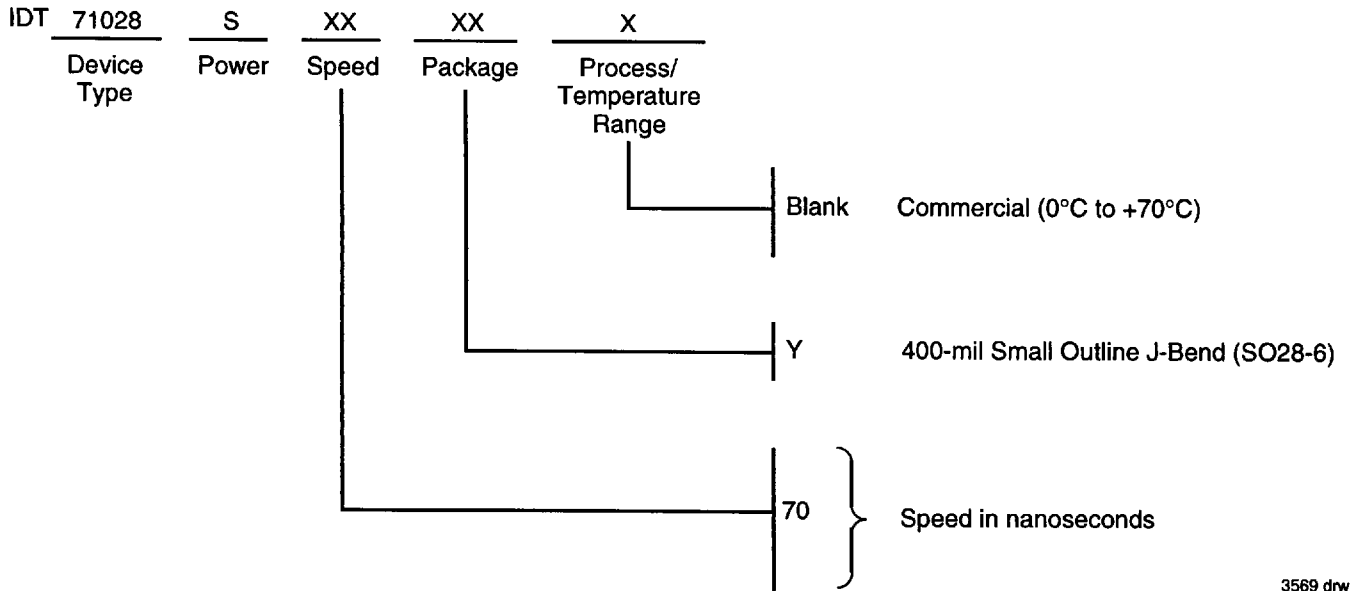
**TIMING WAVEFORM OF WRITE CYCLE NO.2 ( $\overline{CS}$  CONTROLLED TIMING)<sup>(1,2,5)</sup>**



**NOTES:**

1.  $\overline{WE}$  or  $\overline{CS}$  must be HIGH during all address transitions.
2. A write occurs during the overlap of a LOW  $\overline{CS}$  and a LOW  $\overline{WE}$ .
3.  $\overline{OE}$  is continuously HIGH. If during a  $\overline{WE}$  controlled write cycle  $\overline{OE}$  is LOW,  $t_{WP}$  must be greater than or equal to  $t_{WHZ} + t_{DW}$  to allow the I/O drivers to turn off and data to be placed on the bus for the required  $t_{DW}$ . If  $\overline{OE}$  is HIGH during a  $\overline{WE}$  controlled write cycle, this requirement does not apply and the minimum write pulse is as short as the specified  $t_{WP}$ .
4. During this period, I/O pins are in the output state, and input signals must not be applied.
5. If the  $\overline{CS}$  LOW transition occurs simultaneously with or after the  $\overline{WE}$  LOW transition, the outputs remain in a high-impedance state.
6. Transition is measured  $\pm 200\text{mV}$  from steady state.

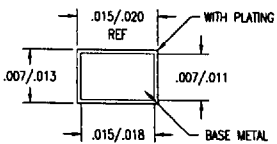
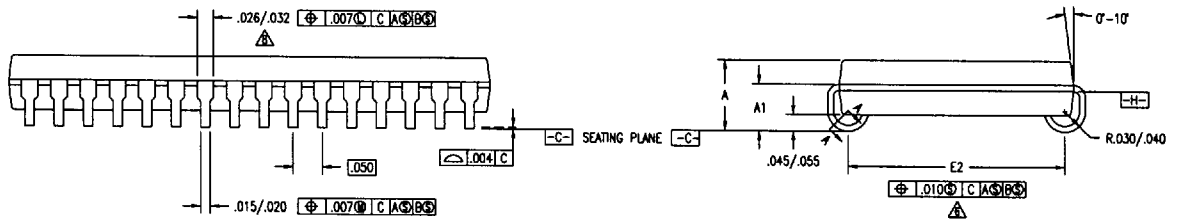
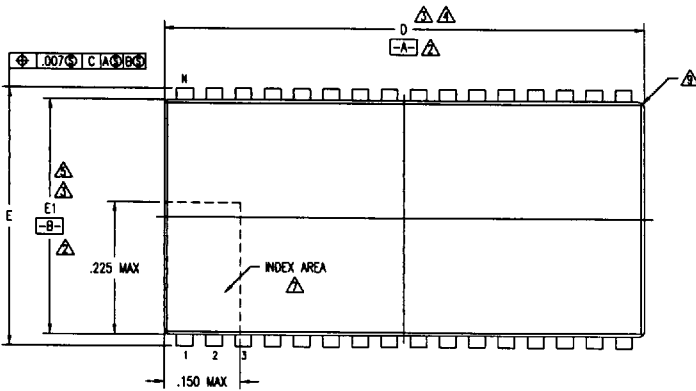
**ORDERING INFORMATION**



3569 drw 09

PACKAGE DIAGRAM OUTLINES  
SOJ (Continued)

REVISIONS				
DCN	REV	DESCRIPTION	DATE	APPROVED
20287	00	INITIAL RELEASE	04/11/91	A. KATZ
21863	01	ADD 28 LD	01/24/92	T. VU
27321	02	ADD A2 DIM	11/14/94	T. VU
27645	03	REDRAW TO JEDEC FORMAT	03/15/95	T. VU
27945	04	ADD 44 LD	06/25/95	



SECTION A-A

TOLERANCES UNLESS SPECIFIED		Integrated Device Technology, Inc. 2975 Stonder Way, Santa Clara, CA 95054 PHONE: (408) 727-8118 FAX: (408) 492-8674 TWC: 910-338-2070
DECIMAL	ANGULAR	
XX±	±	
XXXX		
XXXX±		
APPROVALS	DATE	TITLE
DRWN <i>dt</i>	02/15/96	PB PACKAGE OUTLINE 400" BODY WIDTH SOJ .050" PITCH
CHECKED		
SIZE	DRAWING No.	REV
C	PSC-4033	04
DO NOT SCALE DRAWING		

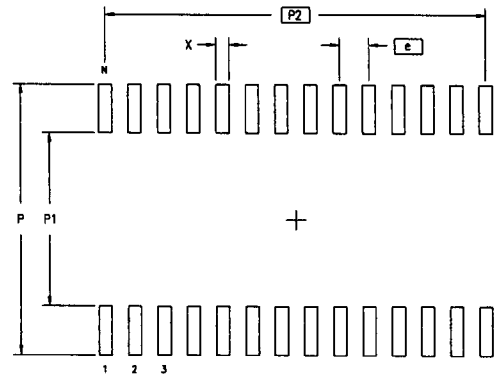


PACKAGE DIAGRAM OUTLINES  
SOJ (Continued)

REVISIONS				
DCN	REV	DESCRIPTION	DATE	APPROVED
20267	00	INITIAL RELEASE	04/11/91	A. KATZ
21863	01	ADD 28 LD	01/24/92	T. WU
27321	02	ADD A2 DIM	11/14/94	T. WU
27645	03	REDRAW TO JEDEC FORMAT	03/15/95	T. WU
27945	04	ADD 44 LD	06/25/95	

SYMBOL	JEDEC # S028-6				JEDEC # S032-3				JEDEC # S044-1			
	JEDEC VARIATION			NOTE	JEDEC VARIATION			NOTE	JEDEC VARIATION			NOTE
	AA	MIN	NOM		MAX	AB	MIN		NOM	MAX	AE	
A	.131	.138	.145		.131	.138	.145		.131	.138	.145	
A1	.082	-	-		.082	-	-		.082	-	-	
D	.720	.725	.730	3,4	.820	.825	.830	3,4	1.120	1.125	1.130	3,4
E	.435	.440	.445		.435	.440	.445		.435	.440	.445	
E1	.395	.400	.405	3,5	.395	.400	.405	3,5	.395	.400	.405	3,5
E2	.360	.370	.380	6	.360	.370	.380	6	.360	.370	.380	6
N	28				32				44			

LAND PATTERN DIMENSIONS



NOTES:

- 1 ALL DIMENSIONING AND TOLERANCING CONFORM TO ANSI Y14.5M-1982
- 2 DATUMS  $-A-$  AND  $-B-$  TO BE DETERMINED AT DATUM PLANE  $-H-$
- 3 DIMENSIONS D AND E1 ARE TO BE DETERMINED AT DATUM PLANE  $-H-$
- 4 DIMENSION D DOES NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS. MOLD FLASH, PROTRUSIONS AND GATE BURRS SHALL NOT EXCEED .006 PER SIDE
- 5 DIMENSION E1 DOES NOT INCLUDE INTERLEAD FLASH OR PROTRUSIONS. INTERLEAD FLASH OR PROTRUSIONS SHALL NOT EXCEED .010 PER SIDE
- 6 DIMENSION E2 TO BE DETERMINED AT SEATING PLANE  $-C-$  CONTACT POINT
- 7 DETAIL OF PIN 1 IDENTIFIER IS OPTIONAL BUT MUST BE LOCATED WITHIN THE ZONE INDICATED
- 8 LEAD WIDTH DIMENSION DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION IS .005 IN EXCESS OF THE LEAD WIDTH DIMENSION AT MAXIMUM MATERIAL CONDITION
- 9 EXACT SHAPE OF EACH CORNER IS OPTIONAL
- 10 ALL DIMENSIONS ARE IN INCHES
- 11 THIS OUTLINE CONFORMS TO JEDEC PUBLICATION 95 REGISTRATION MO-061, VARIATION AA, AB & AE

	MIN	MAX	MIN	MAX	MIN	MAX
P	.458	.466	.458	.466	.458	.466
P1	.290	.294	.290	.294	.290	.294
P2	.650 BSC		.750 BSC		1.050 BSC	
X	.018	.026	.018	.026	.018	.026
e	.050 BSC		.050 BSC		.050 BSC	
N	28		32		44	

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DECIMAL	ANGULAR	
XXX±	2	
XXXX±		
XXXX±		
APPROVALS	DATE	TITLE
DRAWN Ad	02/15/98	PB PACKAGE OUTLINE
CHECKED		.400" BODY WIDTH SOJ
		.050" PITCH
		SIZE C
		DRAWING No. PSC-4033
		REV 04